

17

20. The super-junction semiconductor device according to claim **16**, wherein the channel stopper region and the partition regions form pn-junctions therebetween.

21. The super-junction semiconductor device according to claim **16**, wherein one or more of the partition regions are surrounded by the channel stopper region and the drift regions in a cross section parallel to the first major surface. 5

18

22. The super-junction semiconductor device according to claim **16**, wherein the impurity concentration in the channel stopper regions is equal to or lower than the impurity concentration in the drift regions.

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